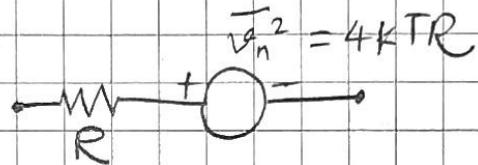
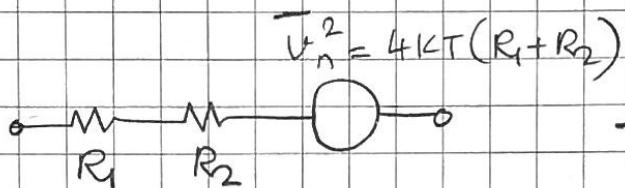
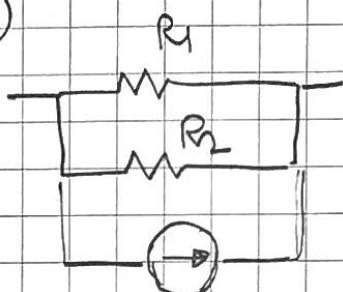
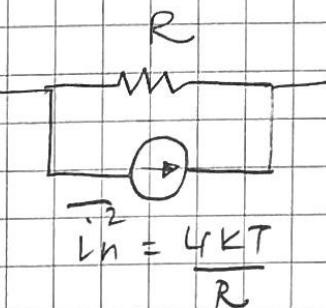


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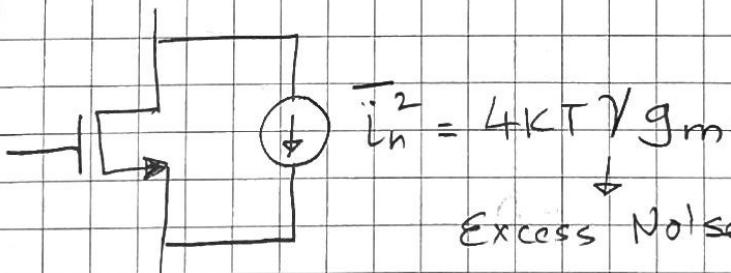
NOISE

RecapNoiseless

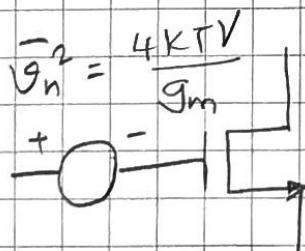
Repeat
Motivation: Why we are studying
NOISELESS



$$\overline{i_n^2} = \frac{4KTR}{(R_1 || R_2)}$$

MOSFETThermal Noise

Excess Noise Coeff. = $2/3$ long ch
= $2 - 3$ sh. ch.



r_o - Not physical resistor
- does not produce noise

MOS FLICKER NOISE

Mos in saturation region.

$\frac{V_n^2}{f} = \frac{k_1/f}{C_{ox} W L} \cdot \frac{1}{f}$

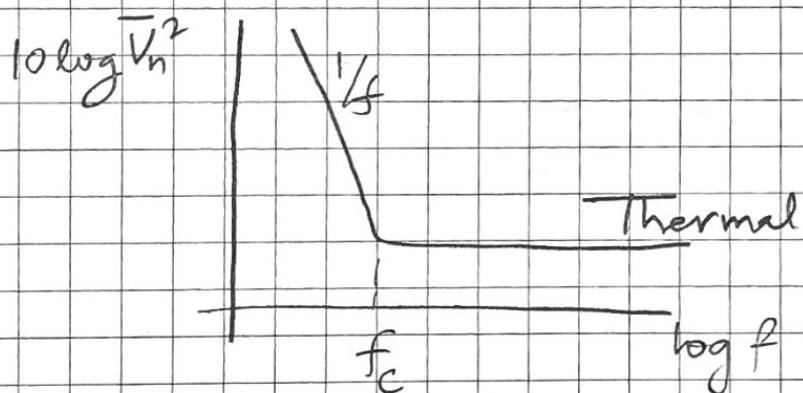
process dependent $10^{-25} V^2 F$

Area ↑ - flicker ↓

Pmos - better $1/f$

hole transport in buried channel

$1/f$ corner

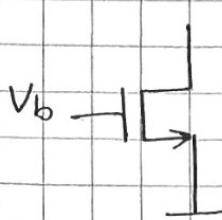


$$f_c = \frac{k'/f}{4kT} \sqrt{\frac{g_m}{WL C_{ox}}} \omega_T$$

2a

Example: Calculate Thermal & flicker noise

for nmos current source. (BW - 1kHz - 10MHz)



$$\text{Assume } g_m = 1 \text{ m.s'}$$

$$C_{gs} = 50 \text{ fF}$$

$$K_{1/f} = 10^{-25} \text{ V}^2 \text{ F}$$

$$(\text{integrated}) \overline{i_{n,\text{thermal}}^2} = 4kT/gm(10^7 - 10^3)$$

$$= 4 \times 1.38 \times 10^{-23} \times 300 \times \frac{2}{3} \times 1 \times 10^{-3} \times 10^7$$

$$= 1.1 \times 10^{-16} \text{ A}^2$$

$$\overline{i_{n,\text{rms}}} = 10.48 \text{ nA rms.} \quad (\text{integrated})$$

FLICKER NOISE

$$\overline{i_{n,f}^2} = \frac{K_{1/f}}{C_{ox}WL} \times \frac{1}{f} \times g_m^2$$

$$= \frac{10^{-25} \text{ V}^2 \text{ F}}{50 \text{ fF}} \times \frac{(1 \text{ m.s'})^2}{f} = \frac{2 \times 10^{-18}}{f} \text{ (A}^2/\text{Hz)}$$

Total $1/f$ noise (integrated)

$$= \int_{1\text{K}}^{10\text{M}} \frac{2 \times 10^{-18}}{f} df = 2 \times 10^{-18} \ln\left(\frac{10\text{M}}{1\text{K}}\right)$$

$$= 18.42 \times 10^{-18} \text{ A}^2$$

$$\overline{i_{n,f,\text{rms}}} = 4.29 \text{ nA rms.}$$



$$\overline{\ln \frac{1}{f}} = K' \ln \left(\frac{f_H}{f_L} \right)$$

(total integrated noise)

$f_L \rightarrow 0 \rightarrow$ Extremely Slow noise components.

$0.01 \text{ Hz} \rightarrow 10 \text{ s} ; 10^{-6} \text{ Hz} \rightarrow 1 \text{ day}$

@ Slow rate - noise indistinguishable from thermal drift & aging.

* Voice Band ($20 \text{ Hz} - 20 \text{ kHz}$)

$\frac{1}{f}$ below 20 Hz - insignificant corruption of signal.

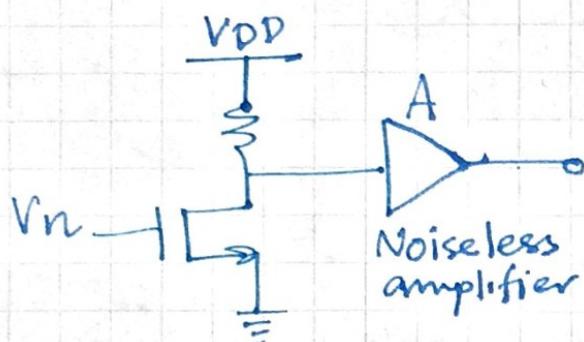
* Total integrated $\frac{1}{f}$ noise = $K' \ln \left(\frac{f_H}{f_L} \right)$

$$K' \ln (10000) = 9.21 \text{ K}'$$

$$K' \ln (1 \times 10^6) = 13.8 \text{ K}'$$

Taking f_L lower doesn't ~~increase~~ increase integrated noise as fast. - due to "ln" function.

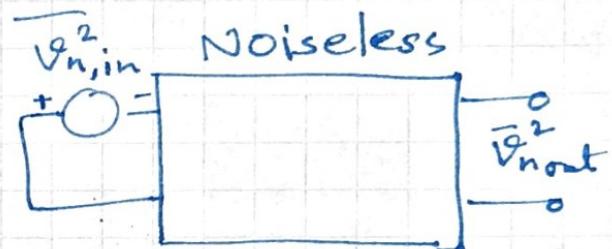
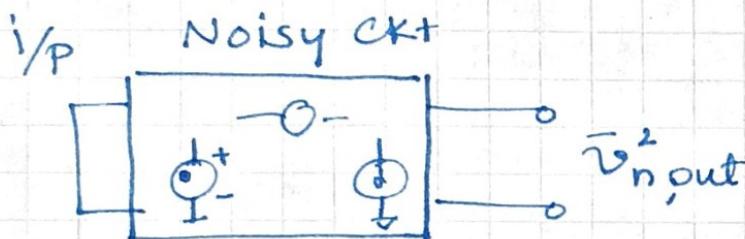
Concept of input referred noise.



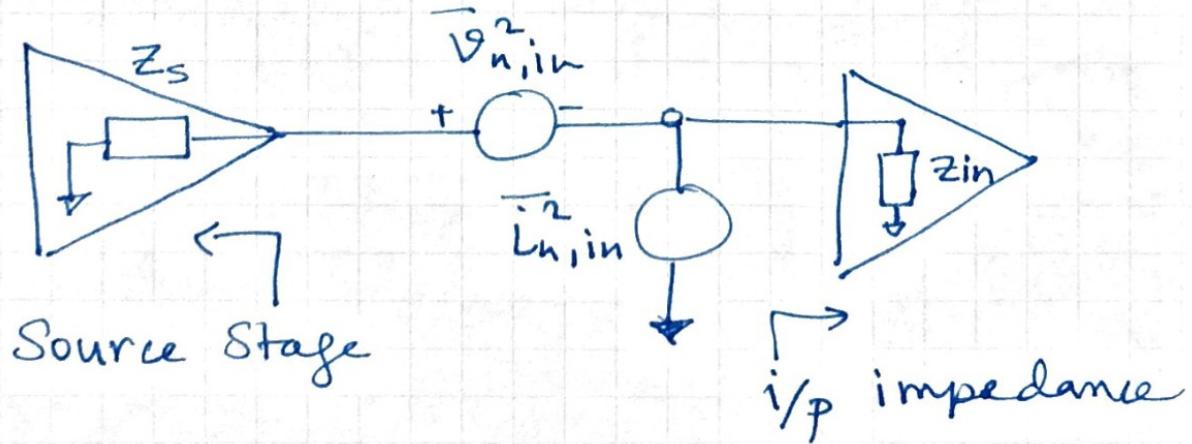
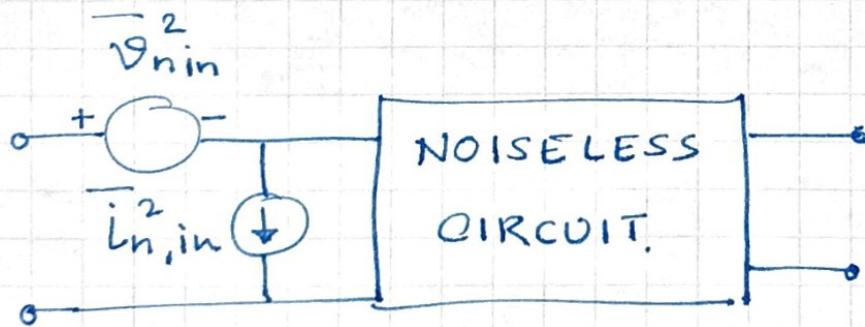
As $A \uparrow$ o/p noise \uparrow .

$\rightarrow A \uparrow$ Signal \uparrow .

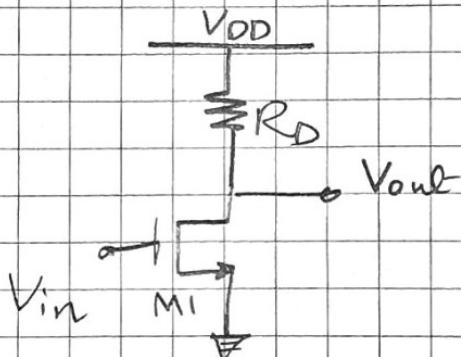
SNR - i/p referred noise.



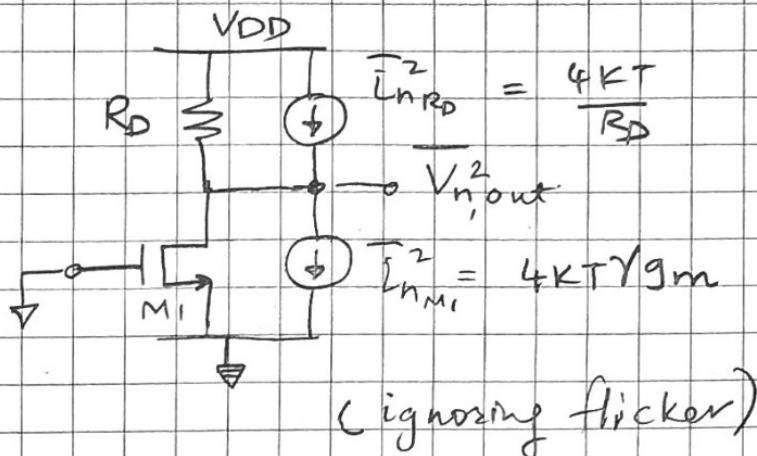
* To account for ~~input~~ impedance of the circuit & source impedance.



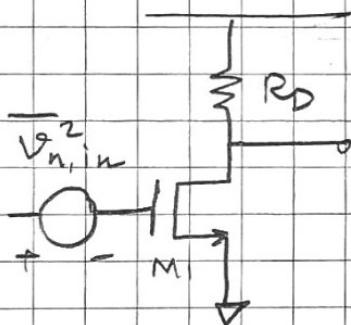
Noise Analysis Examples



\Rightarrow



$$\overline{V_{n,out}^2} = \left(\frac{4KT}{R_D} + 4KT \gamma_m \right) R_D^2 \quad (R_D \ll r_o)$$

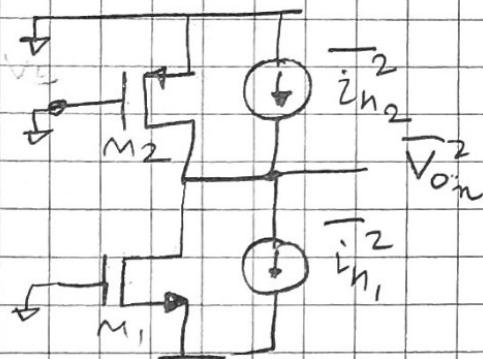
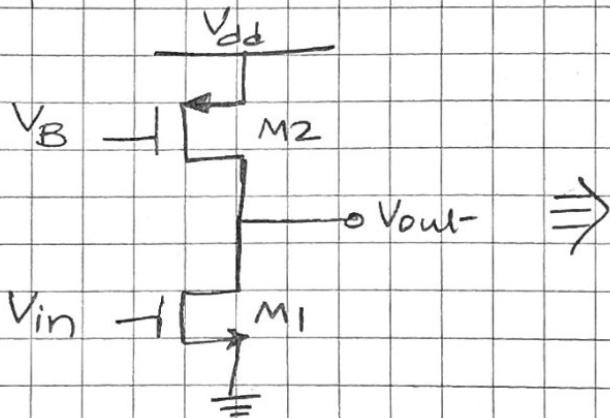


$$\overline{V_{n,in}^2} = \frac{\overline{V_{n,out}^2}}{A_v^2} = \frac{\overline{V_{n,out}^2}}{(g_m R_D)^2}$$

$$= \left(\frac{4KT}{R_D} + 4KT \gamma_m \right) \frac{R_D^2}{(g_m \cdot R_D)^2}$$

$$= \frac{4KT}{g_m} \left(\frac{1}{g_m R_D} + \gamma \right)$$

(ONLY THERMAL NOISE
CONSIDERED)

Example 2.CS AMP.

$$\overline{V_{o,n}^2} = (4kT \gamma_n g_{m_1} + 4kT \gamma_p g_{m_2}) r_{out}^2$$

$$\text{Gain} = A_g = g_{m_1} r_{out}$$

$$\overline{V_{o,n}^2} = (4kT \gamma_n g_{m_1} + 4kT \gamma_p g_{m_2}) \frac{r_{out}^2}{g_{m_1}^2 r_{out}^2}$$

$$= \frac{4kT \gamma_n}{g_{m_1}} + \frac{4kT \gamma_p}{g_{m_2}} \left(\frac{g_{m_2}}{g_{m_1}} \right)^2$$

\uparrow
i/p referred
due to M_1 only.

\rightarrow Keeping g_{m_1} high.

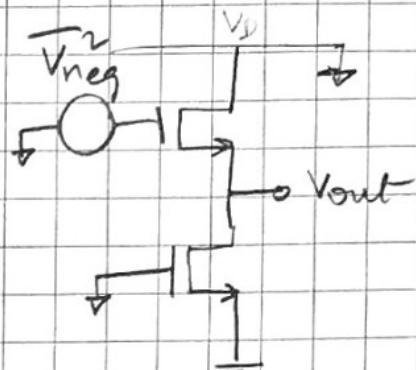
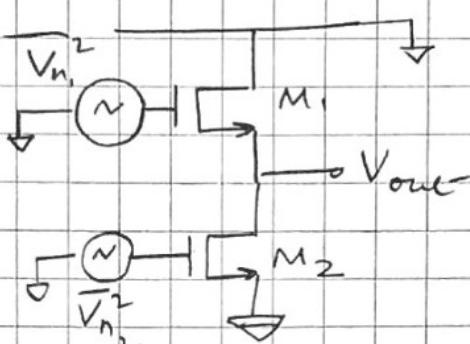
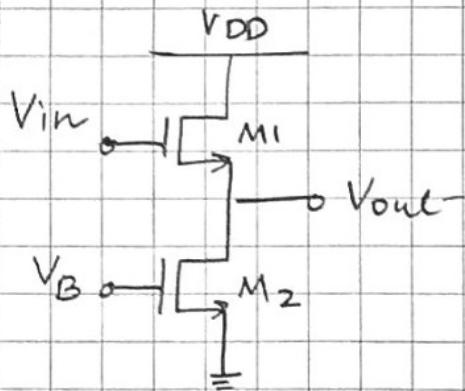
Reduces contributions of current source.

$$= \overline{V_{n_1}^2} + \overline{V_{n_2}^2} \left(\frac{g_{m_2}}{g_{m_1}} \right)^2$$

\uparrow
Gate Refered Noise of Each transistor.

Example 3

SOURCE FOLLOWER



Using Superposition

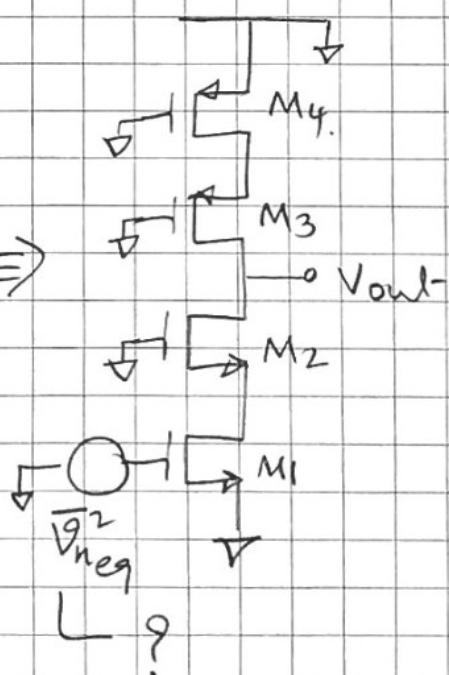
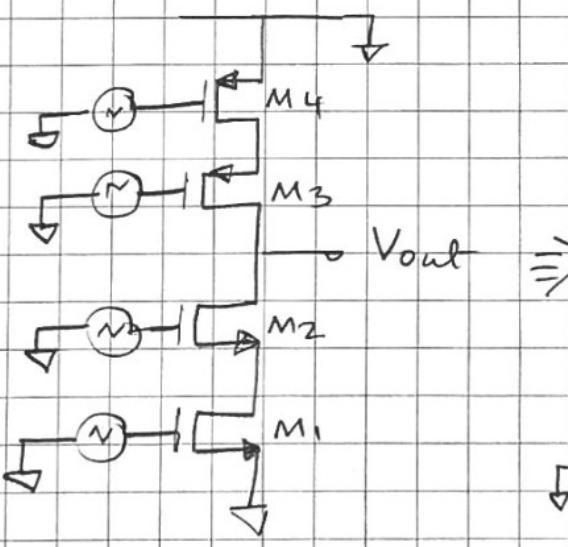
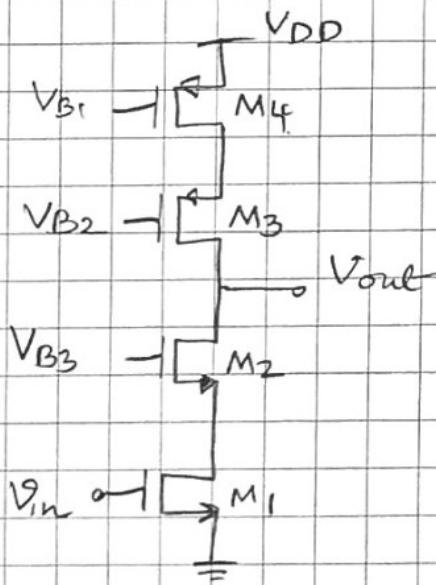
$$\overline{V_{out}}^2 = \overline{V_{n1}}^2 + \overline{V_{n2}}^2 \left(\frac{g_{m2}}{g_{m1}} \right)^2 = \overline{V_{nega}}^2$$

(Since $A_v = 1$
unity gain)

$$\overline{V_{nega}}^2 = \left(\overline{V_{n1}}^2 + \overline{V_{n2}}^2 \left(\frac{g_{m2}}{g_{m1}} \right)^2 \right)$$

Example 4

CASCODE CS AMP.

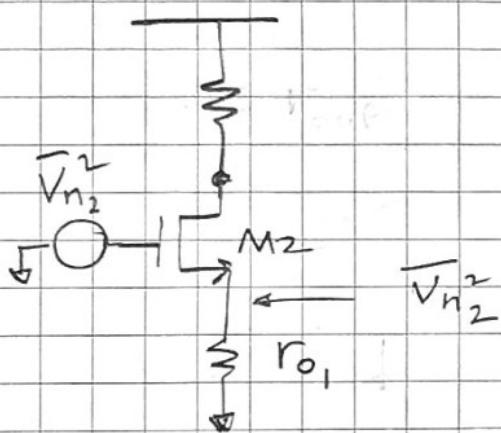


Consider M_1 & M_4 only.

$$\overline{V_{\text{neg}}}^2 = \overline{V_{n_1}}^2 + \overline{V_{n_4}}^2 \left(\frac{g_{m_4}}{g_{m_1}} \right)^2$$

(Based on Previous example)

Imp Point Cascode \leftrightarrow Noise ?



$$\overline{V_{n_{\text{out}}}^2} = \frac{\overline{V_{n_2}^2}}{r_o^2} \times r_{\text{out}}^2$$

if p referred to gate of M_1

$$\begin{aligned} \overline{V_{\text{neg}}}^2 &= \frac{\overline{V_{n_2}^2}}{r_{o_1}^2} \times \frac{r_{\text{out}}^2}{g_{m_1}^2 r_{\text{out}}^2} \\ &= \frac{\overline{V_{n_2}^2}}{(g_{m_1} r_{o_1})^2} \end{aligned}$$

M

Insight Cascode Noise

Contributions divided by $(g_m r_o)$

Large #

Same applicable to M_3 .

By superposition

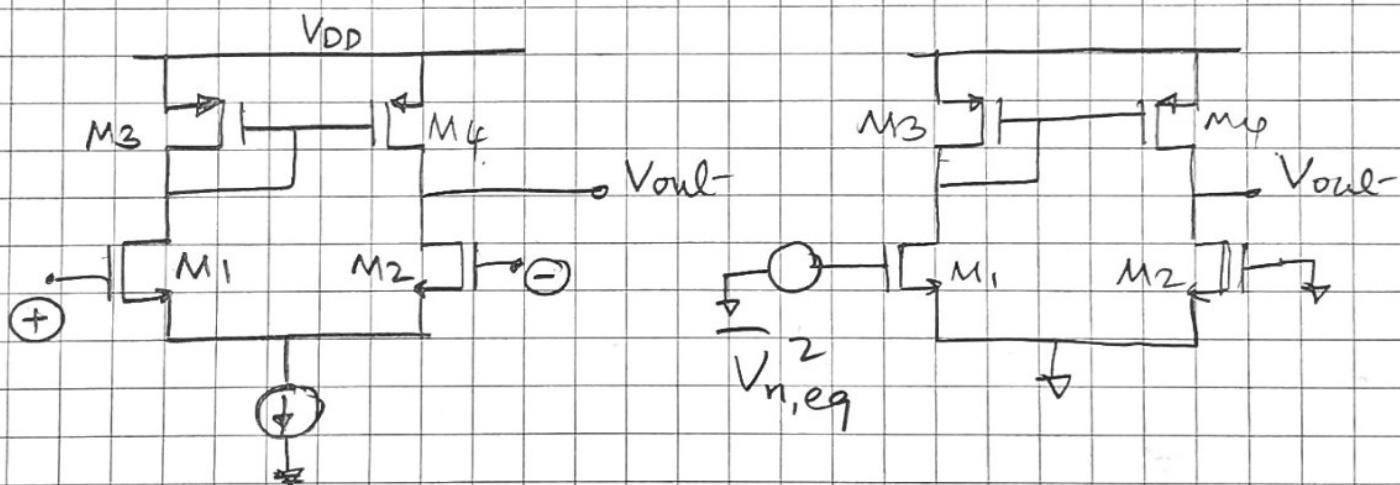
$$\overline{V_{n_{eq}}^2} = \overline{V_{n_1}^2} + \overline{V_{n_4}^2} \left(\frac{g_{m_4}}{g_{m_1}} \right)^2 + \overline{V_{n_2}^2} \left(\frac{1}{(g_{m_1} r_o)_1} \right)^2 + \overline{V_{n_3}^2} \left(\frac{1}{(g_{m_1} r_o)_4} \right)^2$$

Cascode contributions

Cascode generally does not degrade noise performance.

Example 25

CMOS DIFF AMP



$$\overline{V_{n_{eq}}^2} = 2 \left[\overline{V_1^2} + \overline{V_3^2} \left(\frac{g_{m_3}}{g_{m_1}} \right)^2 \right]$$

(PROVE URSELF)